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Last Name = **HAYASHI**
First Name = **HIROKAZU**

Application#	Patent#	Status	Date Filed	Title	Inventor Name
11002333	Not Issued	030	12/03/2004	METHOD OF EVALUATING SEMICONDUCTOR DEVICE	HAYASHI, HIROKAZU
10293011	Not Issued	030	11/16/2004	SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME	HAYASHI, HIROKAZU
10913271	Not Issued	020	09/03/2004	ESD PROTECTION DEVICE MODELING METHOD AND ESD SIMULATION METHOD	HAYASHI, HIROKAZU
10710238	Not Issued	030	02/19/2004	EVALUATION TEG FOR SEMICONDUCTOR DEVICE AND METHOD OF EVALUATION	HAYASHI, HIROKAZU
10668261	Not Issued	030	09/24/2003	METHOD FOR MODELING SEMICONDUCTOR DEVICE AND NETWORK	HAYASHI, HIROKAZU
10652712	Not Issued	030	01/17/2003	METHOD FOR MODELING SEMICONDUCTOR DEVICE PROCESS	HAYASHI, HIROKAZU
09891402	65565712	150	06/27/2001	SOI STRUCTURE SEMICONDUCTOR DEVICE AND A FABRICATION METHOD THEREOF	HAYASHI, HIROKAZU
02781424	65246251	150	02/13/2001	METHOD FOR MODELING DIFFUSION OF IMPURITIES IN A SEMICONDUCTOR	HAYASHI, HIROKAZU
03519856	62776841	150	02/06/2000	A METHOD OF FABRICATING A SOI STRUCTURE SEMICONDUCTOR DEVICE	HAYASHI, HIROKAZU
02425362	6531028	150	02/08/1999	PROFILE EXTRACTION METHOD AND PROFILE EXTRACTION APPARATUS	HAYASHI, HIROKAZU
08140552	5422019	150	10/25/1993	PROJECTED IMAGE DISPLAYING APPARATUS AND A METHOD OF CORRECTING COLOR UNLEVELNESS THEREIN	HAYASHI, HIROKAZU
07701632	5299101	150	05/15/1991	CATIONIC ELECTRODEPOSITION COATING COMPOSITION	HAYASHI, HIROKAZU
02118720	5294361	150	03/03/1989	ELECTRODEPOSITION COATING COMPOSITION	HAYASHI, HIROKAZU
07292001	Not Issued	166	01/03/1989	CATIONIC ELECTRODEPOSITION COATING COMPOSITION	HAYASHI, HIROKAZU

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Chun-Yen Chang, Chih-Yung Lin, Jin-Wen Choi, Hsu, C.C.-H., Hong-Tz. Pan

Electron Device Letters, IEEE Computer-Aided Design of Integrated Circuits and Systems, IEEE Transaction

Volume 15, Issue 11, Nov. 1994 Page(s): 437 - 439

Digital Object Identifier: 10.1109/5.334659

AbstractPlus | Full Text: EDE(242 KB) IEEE JNL

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7. Reverse short-channel effect due to lateral diffusion of point-defect induced source/drain ion implantation

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Lutz, J.; Venkatasen, S.; Electron Device Letters, IEEE Volume 16, Issue 9, Sept. 1995 Page(s): 373 - 375

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9. Reduction of the reverse short channel effect in thick SOI MOSFETs

Troudiatis, D.; Sams, C.; Kukuruzas, D.N.; Kova, P.; Itoh, E.; Electron Device Letters, IEEE Volume 18, Issue 3, March 1997 Page(s): 90 - 92

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Rousseau, P.M.; Crowder, S.W.; Griffin, P.B.; Plummer, J.D.; Electron Device Letters, IEEE Volume 18, Issue 12, Dec. 1997 Page(s): 442 - 444

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Chung, S.S.; Shu-Ling Cheng; Lee, R.G.-H.; Song-Nian Kuo; Mong-Song Liu

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IEEE STD IEEE Standard

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27. Reverse short-channel effects and channel-length engineering in deep-submicron modeling and optimization

Bin Yu; Newnam, E.; Noda, K.; Cherming Hu; VLSI Technology, 1996, Digest of Technical Papers, 1996 Symposium on 11-13 June 1996 Page(s):162 - 163 Digital Object Identifier 10.1109/MLST.1996.507833 AbstractPlus | Full Text: EDE(284 KB) IEEE CNF

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